# EPISTAR

AIGaInP PX-series LED Chip

## > Mechanical Specification:

- (1) Dimension
  - Chip size: 42 mil x 42 mil (1070±25 μm x 1070±25 μm)
  - Thickness: 8.8 mil (225±25 μm)
  - P bonding pad: 4.7 mil (120 $\pm$ 10  $\mu$ m)

#### (2) Metallization

- Topside P electrode: Au alloy(x2)
- Backside N electrode: Au alloy





N-electrode

### Features:

- · High luminous intensity
- · Thin film structure
- · Vertical electrode
- · High driving current

#### **Applications:**

- Traffic signal
- $\cdot$  Lighting

## > Electro-optical Characteristics at 25°C:

| Parameter                            | Symbol |     | Condition  | Min.  | Тур. | Max. | Unit |
|--------------------------------------|--------|-----|------------|-------|------|------|------|
| Forward Voltage                      | Vf1    |     | lf = 10μΑ  | 1.3   | -    | -    | V    |
|                                      | Vf2    |     | lf = 350mA | -     | 2.2  | 2.6  | V    |
| Reverse Current                      | lr     |     | Vr = 10V   | -     | -    | 5.0  | μΑ   |
| Peak Wavelength                      | λρ     |     | lf = 350mA | -     | 591  | -    | nm   |
| Dominant Wavelength <sup>(1)</sup>   | λd     |     | lf = 350mA | 584   | 589  | 594  | nm   |
| Spectra Half-width                   | Δλ     |     | lf = 350mA | -     | 15   | -    | nm   |
| Luminous Intensity <sup>(2)(3)</sup> | lv     | H16 | lf = 350mA | 15000 | -    | -    |      |
|                                      |        | H17 |            | 17000 | -    | -    | mcd  |
|                                      |        | H18 |            | 19000 | -    | -    |      |

Note:

(1) Basically, the wavelength span is 10nm; however, customers' special requirements are also welcome.

(2) Customers' special requirements are also welcome.

(3) Luminous intensity is measured by EPISTAR's equipment on bare chips.

| Parameter                    | Symbol | Condition                   | Rating      | Unit |
|------------------------------|--------|-----------------------------|-------------|------|
| Forward DC Current           | lf     | Ta = 25°C                   | ≤ 700       | mA   |
| Reverse Voltage              | Vr     | Ta = 25°C                   | ≤ 10        | V    |
| Junction Temperature         | Тј     | -                           | ≤ 125       | °C   |
| Storage Temperature          | Tstg   | Chip                        | -40 ~ +85   | °C   |
|                              |        | Chip-on-tape/storage        | 5 ~ 35      | °C   |
|                              |        | Chip-on-tape/transportation | -20 ~ +65   | °C   |
| Temperature during Packaging | -      | -                           | 280(<10sec) | °C   |

## > Absolute Maximum Ratings:

Note: Maximum ratings are package dependent. The above maximum ratings were determined using a Metal Core Printed Circuit Board (MCPCB) without an encapsulant. Stresses in excess of the absolute maximum ratings such as forward current and junction temperature may cause damage to the LED.

## > Characteristic Curves:





Fig.3 – Relative Intensity (@350mA) vs. Ambient Temperature



Fig.5 – Dominant Wavelength (@350mA) vs. Ambient Temperature



Fig.2 – Forward Current vs. Forward Voltage







Fig.6 – Maximum Driving Forward DC Current vs. Ambient Temperature (De-rating based on Tj max. = 125°C)

